

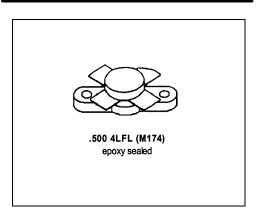
PHONE: (215) 631-9840 FAX: (215) 631-9855

MS1007

RF & MICROWAVE TRANSISTORS HF SSB APPLICATIONS

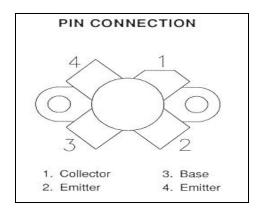
Features

- 30 MHz
- 50 VOLTS
- P_{OUT} = 150 WATTS
- $G_P = 14 \text{ dB MINIMUM}$
- COMMON EMITTER CONFIGURATION



DESCRIPTION:

The MS1007 is a 50V epitaxial silicon NPN planar transistor designed primarily for SSB communications. This device utilizes emitter ballasting to achieve extreme ruggedness under severe operating conditions.



ABSOLUTE MAXIMUM RATINGS (Tcase = 25°C)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	110	V
V _{CEO}	Collector-Emitter Voltage	55	V
V_{EBO}	Emitter-Base Voltage	4.0	V
Ic	Device Current	10	Α
P _{DISS}	Power Dissipation	233	W
TJ	Junction Temperature	+200	°C
T _{STG}	Storage Temperature	-65 to +150	°C

Thermal Data

R _{TH(J-C)}	Thermal Resistance Junction-case	0.75	°C/W
----------------------	----------------------------------	------	------



PHONE: (215) 631-9840 FAX: (215) 631-9855

MS1007

ELECTRICAL SPECIFICATIONS (Tcase = 25°C) STATIC

Symbol	Test Conditions	Value			Unit		
	rest Conditions		Min.	Typ.	Max.	Offic	
BV _{CBO}	I _C = 100mA	$I_E = 0mA$		110			V
BV _{CES}	I _C = 100mA	$V_{BE} = 0V$		110			V
BV _{CEO}	I _C = 100mA	I _B = 0mA		55			V
BV _{EBO}	I _E = 10mA	I _C = 0mA		4.0			V
I _{CEO}	V _{CE} = 30V	I _E = 0 mA				5	mA
I _{CES}	V _{CE} = 60V	I _E = 0mA				5	mA
h _{FE}	V _{CE} = 6V	I _C = 1.4A		18		43.5	

DYNAMIC

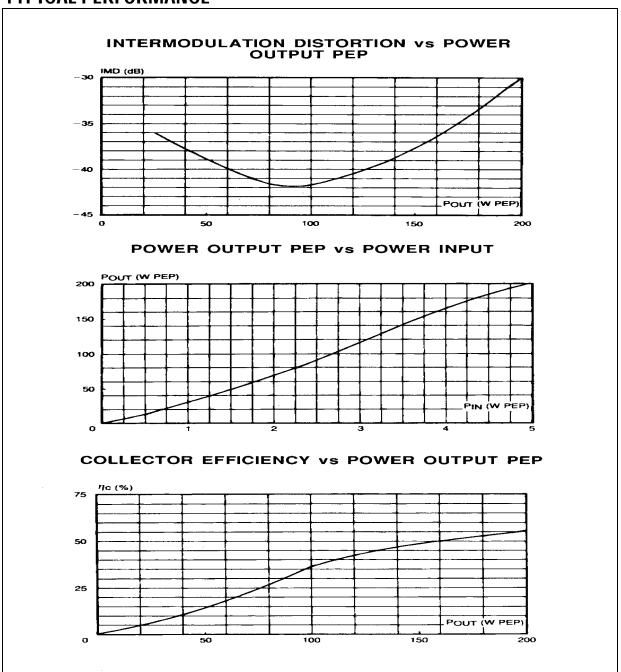
Symbol	Test Conditions			Value			
Syllibol			Min.	Typ.	Max.	Unit	
P _{OUT}	f = 30 MHz	$V_{CE} = 50V$	I _{CQ} = 100mA	150			WPEP
G₽	P _{OUT} = 150WPEP	V _{CE} = 50V	I _{CQ} = 100mA	14			dB
IMD	P _{OUT} = 150WPEP	$V_{CE} = 50V$	I _{CQ} = 100mA			-30	dBc
ης	P _{OUT} = 150WPEP	$V_{CE} = 50V$	I _{CQ} = 100mA	37			%
Сов	f = 1 MHz	$V_{CB} = 50 \text{ V}$				220	pf
Conditions	f1 = 30.000MHz	f2 = 30.001M	lHz				



PHONE: (215) 631-9840 FAX: (215) 631-9855

MS1007

TYPICAL PERFORMANCE





PHONE: (215) 631-9840 FAX: (215) 631-9855

MS1007

PACKAGE MECHANICAL DATA

